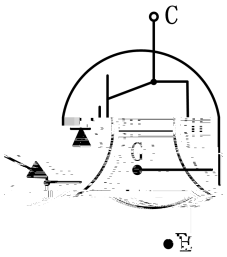
JJMICROELECTRONICS

650V 40A Trench and Field Stop IGBT

JJT40N65HE

TO-247



V_{CES}	Collector-emitter voltage	650	V
V_{GES}	Gate-emitter voltage	±20	V
I_C	Continuous collector current (T_C=25)	80	A
	Continuous collector current (T_C=100)	40	A
I_{CM}	Pulsed collector current, t_p limited by T_{vjmax}	160	A
I_F	Diode continuous forward curren		

CES	Collector-emitter breakdown voltage	$_{GE}$=0V, I_C=250μA	650	-	-	V
CES	Collector-emitter leakage current	$_{CE}$=650V, $_{GE}$=0V	-	-	50	μA
GES	Gate					

G I6

A d c f a c ed a d b ec e a d c a e .

Switching characteristics

$t_{d(on)}$	Turn-on delay time	V_{CC}=400V V_{GE}=0/15V I_C=40A R_G=10 Inductive load	-	32	-	ns
t_r	Rise time		-	59	-	ns
$t_{d(off)}$	Turn-off delay time		-	110	-	ns
t_f	Fall time		-	52	-	ns
E_{on}	Turn-on energy		-	1.2	-	mJ
E_{off}	Turn-off energy		-	0.6	-	mJ
E_{ts}	Total switching energy		-	1.8	-	mJ
$t_{d(on)}$	Turn-on delay time	V_{CC}=400V V_{GE}=0/15V I_C=40A R_G=10 Inductive load T_{vj}=175	-	28	-	ns
t_r	Rise time		-	51	-	ns
$t_{d(off)}$	Turn-off delay time		-	131	-	ns
t_f	Fall time		-	78	-	ns
E_{on}	Turn-on energy		-	1.6	-	mJ
E_{off}	Turn-off energy		-	1.0	-	mJ
E_{ts}	Total switching energy		-	2.6	-	mJ

V_F	Diode forward voltage	I_F=40A	-	1.5	-	V
		I_F=40A, T_{vj}=175	-	1.3	-	V
t_{rr}	Diode reverse recovery time	V_R=400V	-	82	-	ns
I_{rrm}	Diode peak reverse recovery current	I_F=40A	-	15	-	A
Q_{rr}	Diode reverse recovery charge	dI_F/dt =-1200A/μs	-	1620	-	nC
t_{rr}	Diode reverse recovery time	V_R=400V				

Iode

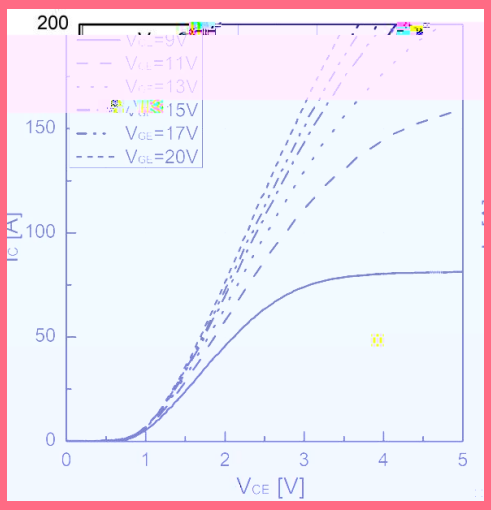


Fig 1. Typical output characteristic (vj=25)

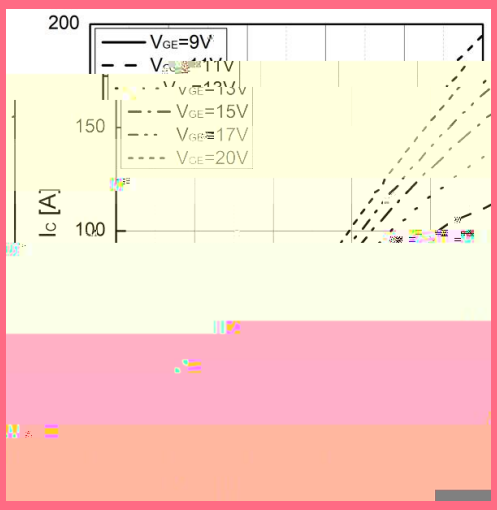


Fig 2. Typical output characteristic(vj=175)



Fig 3. Power dissipation as a function of

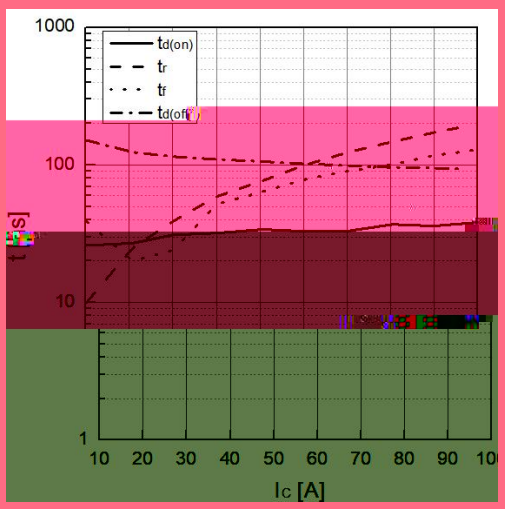


Fig 4. Typical switching time as a function of C

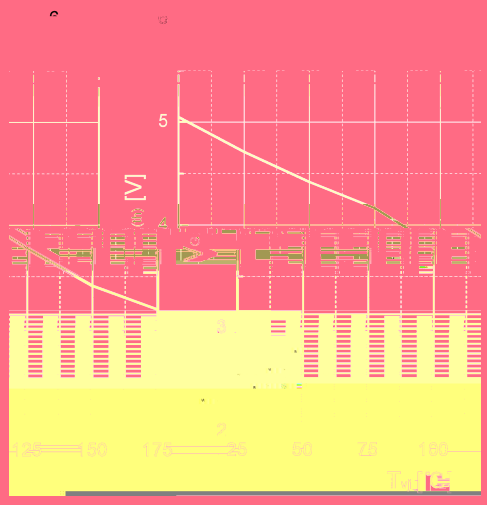


Fig 5. Typical GE(th) as a function of vj (C=1mA)

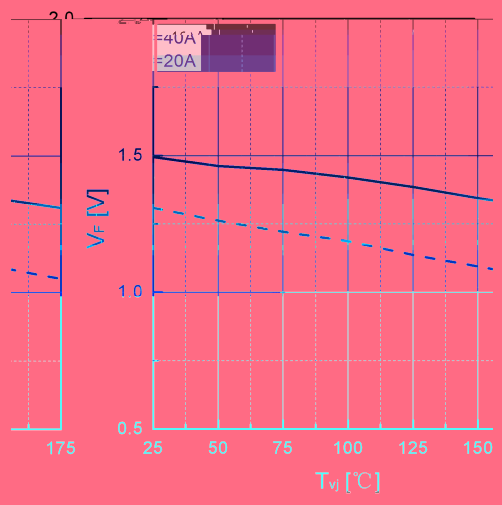
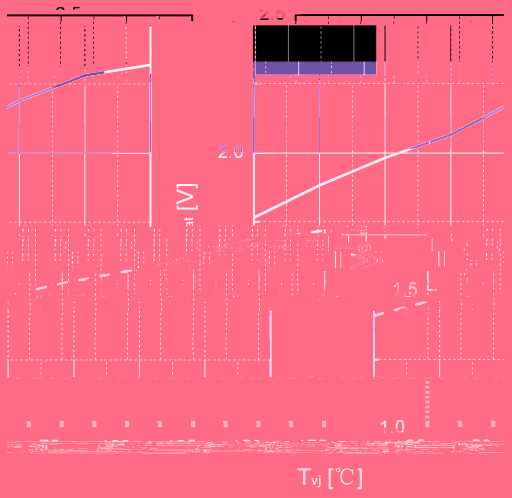


Fig 6. Typical F as a function of vj

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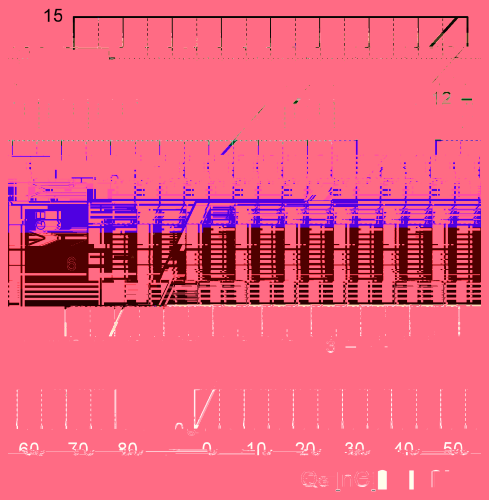


Fig 7. Typical $_{CEsat}$ as a function of $_{vj}$

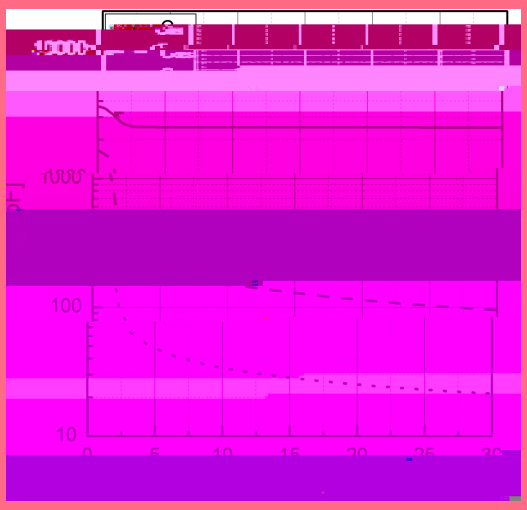


Fig 13. Typical capacitance as a function of $_{CE}$ (f=1Mhz, $_{GE}$=0V)

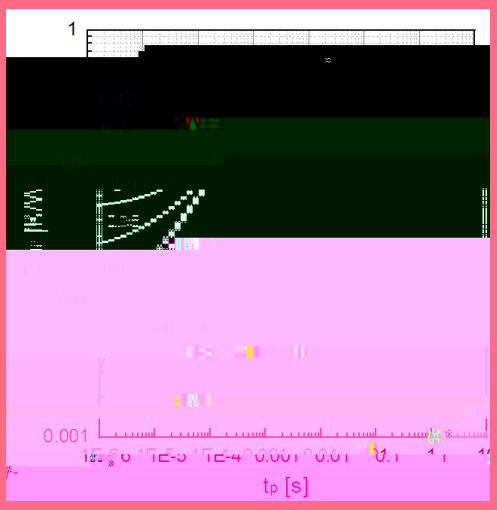
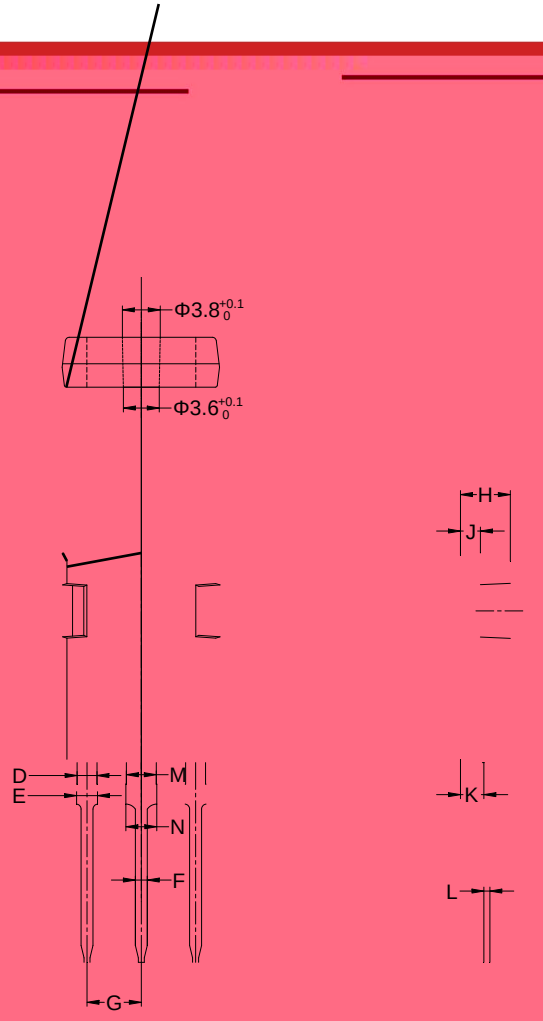


Fig 14. Transient thermal impedance of IGBT

TO-247



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	15.50	15.80	16.10	0.610	0.622	0.634
B	20.80	21.00	21.20	0.819	0.827	0.835
C	19.70	20.00	20.30	0.776	0.787	0.799
D	1.80	2.00	2.20	0.071	0.079	0.087
E	1.90	2.10	2.30	0.075	0.083	0.091
F	1.00	1.20	1.40	0.039	0.047	0.055
G	5.25	-	5.65	0.207	-	0.222
H	4.80	5.00	5.20	0.189	0.197	0.205
J	1.90	2.00	2.10	0.075	0.079	0.083
K	2.20	2.35	2.50	0.087	0.093	0.098
L	0.41	0.60	0.79	0.016	0.024	0.031
M	2.80	3.00	3.20	0.110	0.118	0.126
N	2.90	3.10	3.30	0.114	0.122	0.130

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Date	Revision	Changes
2024-03-06	Rev 1.1	Update
2024-05-17	Rev 1.2	Update
2024-10-22	Rev 1.3	Update
2026-06-25	Rev 1.4	Update thermal

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